

BUR920000140US1

RX MASK: ETCH SHALLOW TRENCH

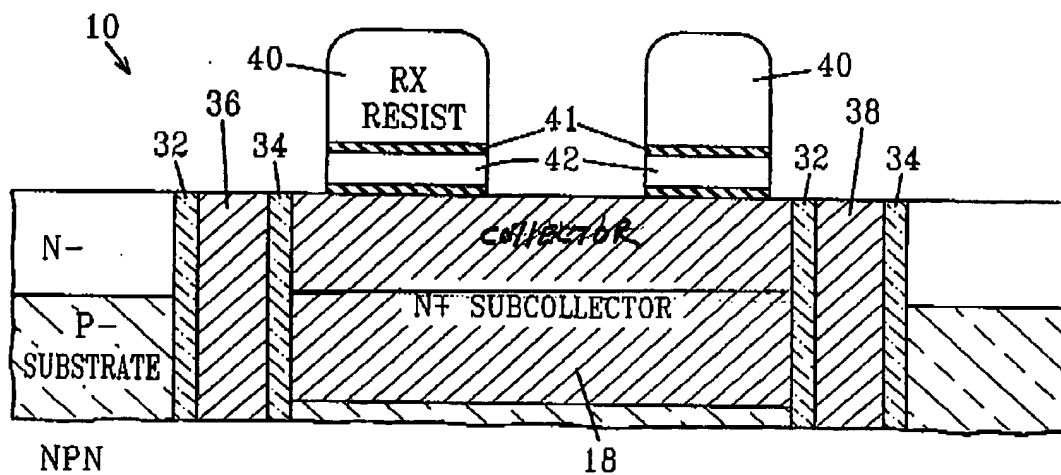


FIG. 5

EL approved  
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AFTER AB TRENCH PLANARIZATION  
AND PAD NITRIDE STRIP

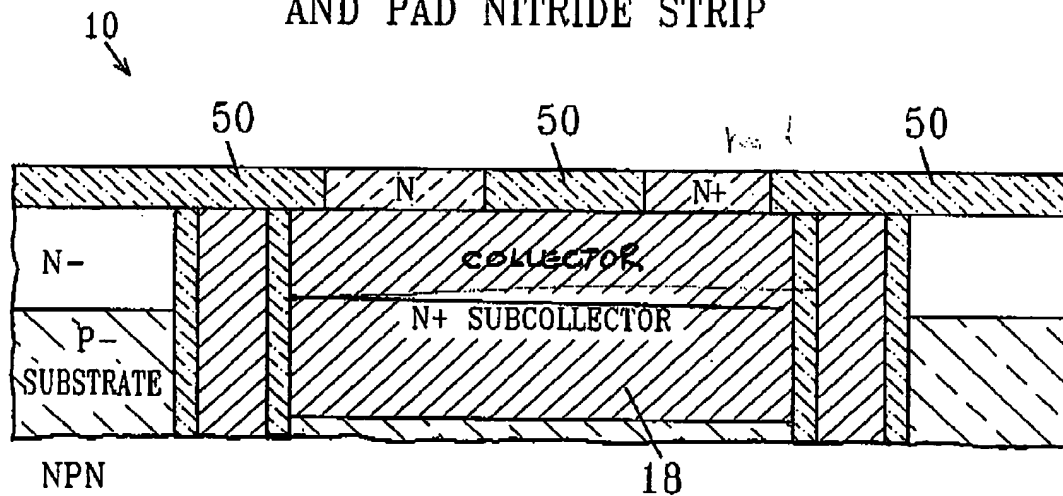


FIG. 6

EL  
approved  
10/3/03

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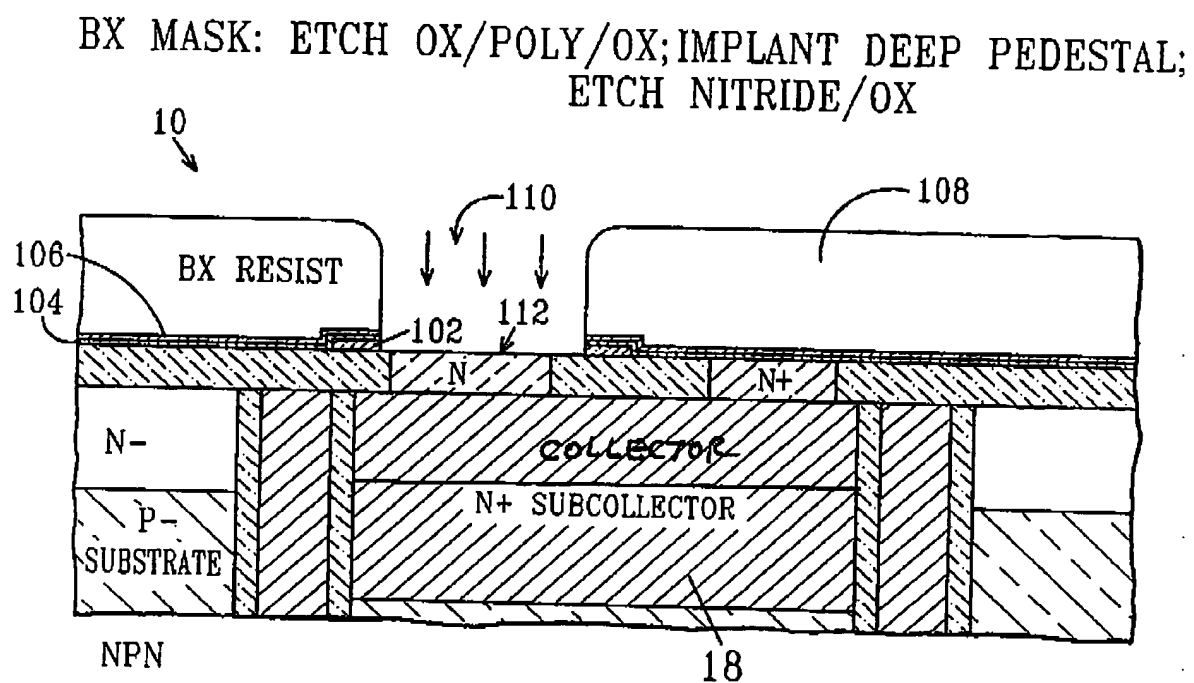


FIG. 7

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## EN MASK: DEFINE EMITTER AND EXTRINSIC BASE

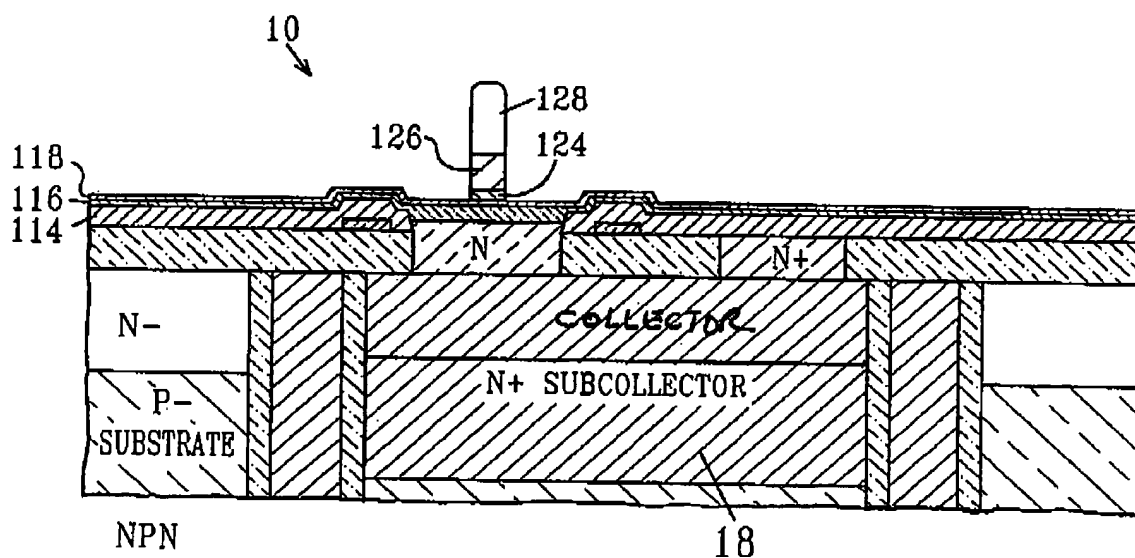


FIG. 9

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## EXTRINSIC BASE IMPLANT

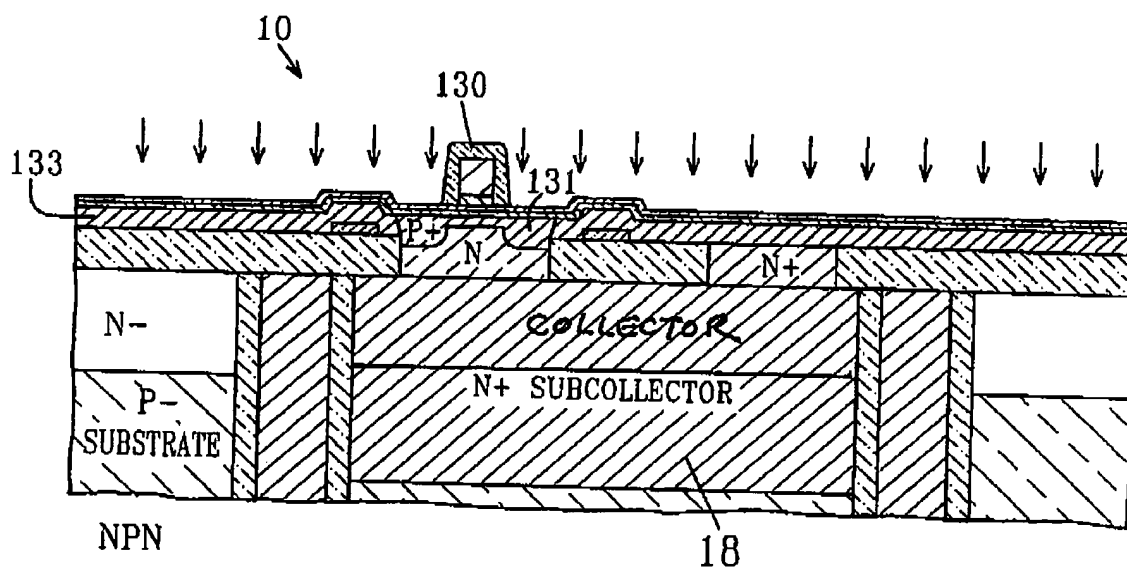


FIG.10

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OP MASK: FORM NPN SPACER  
AND RESISTOR  $\text{TiSi}_x$  BLOCK

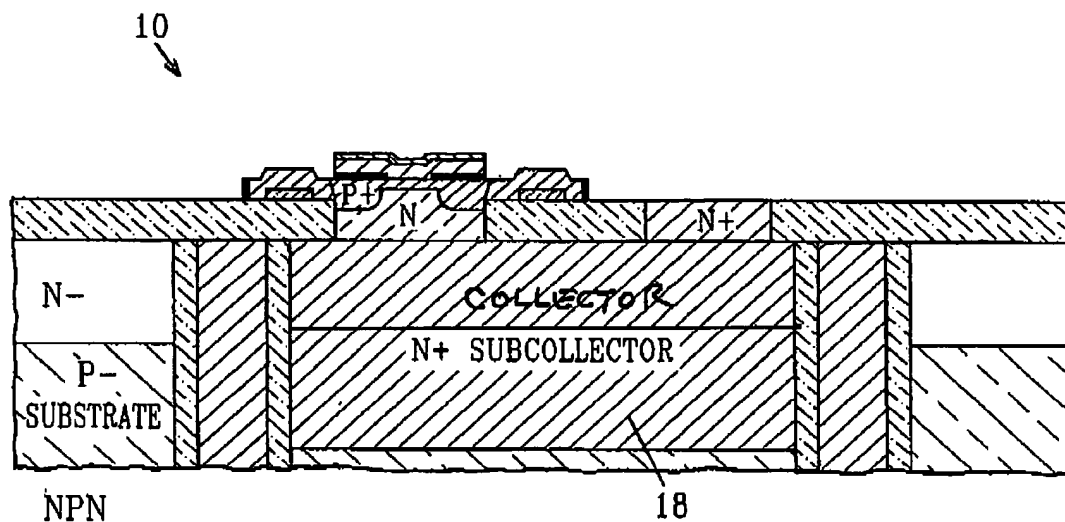


FIG. 15

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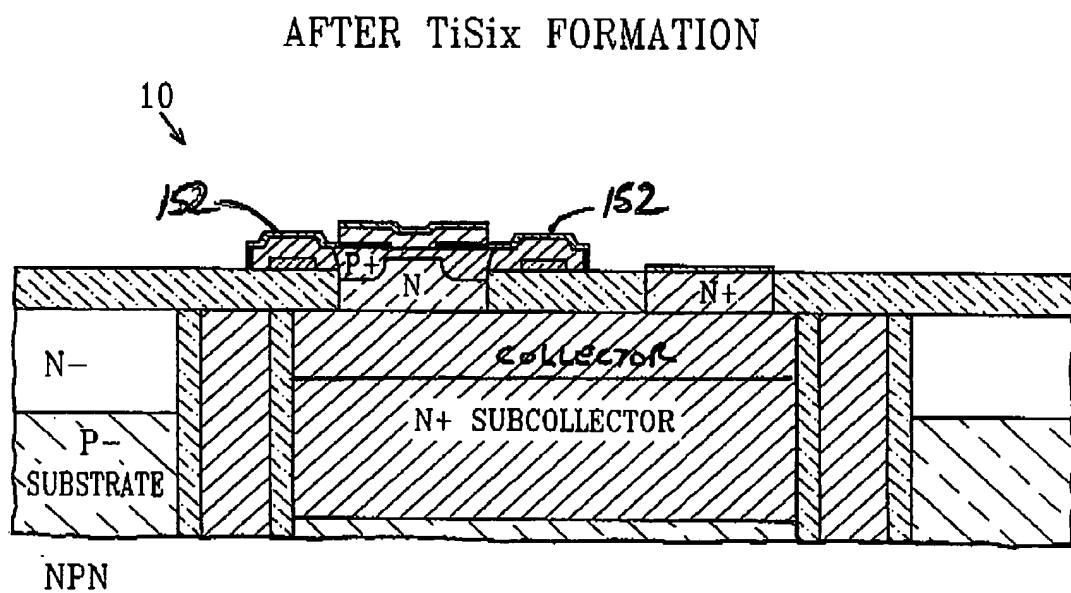


FIG. 16

EL approval  
10/3/03

# SiGe HBT TRANSISTOR

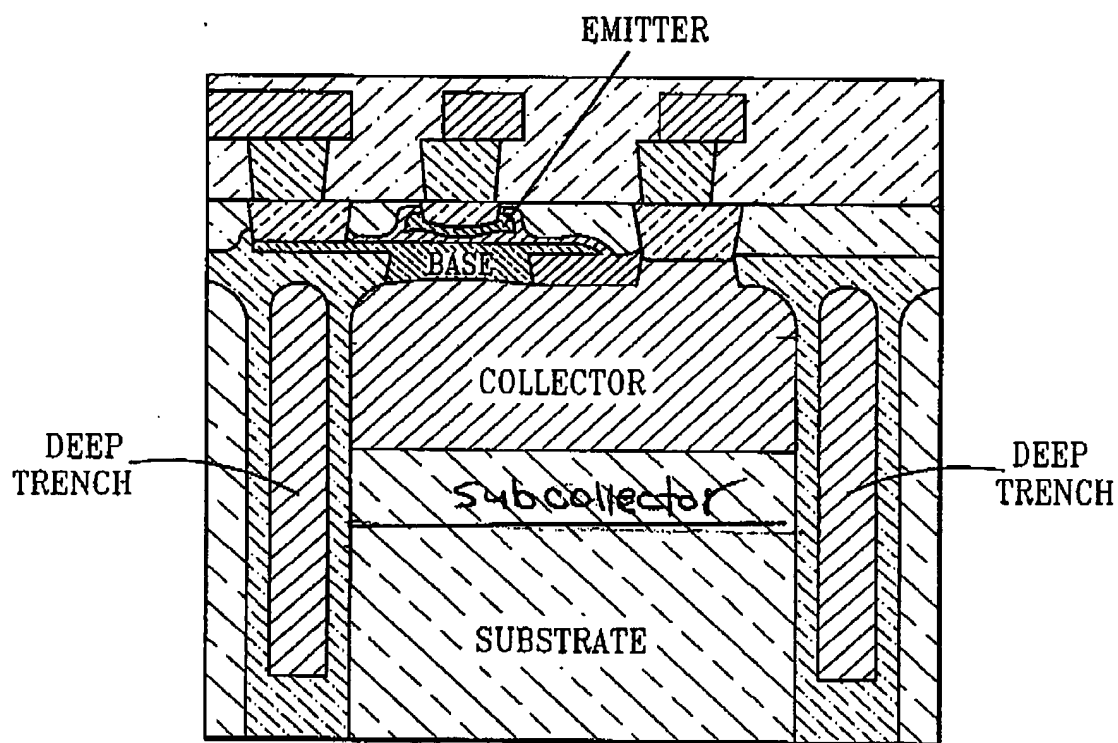
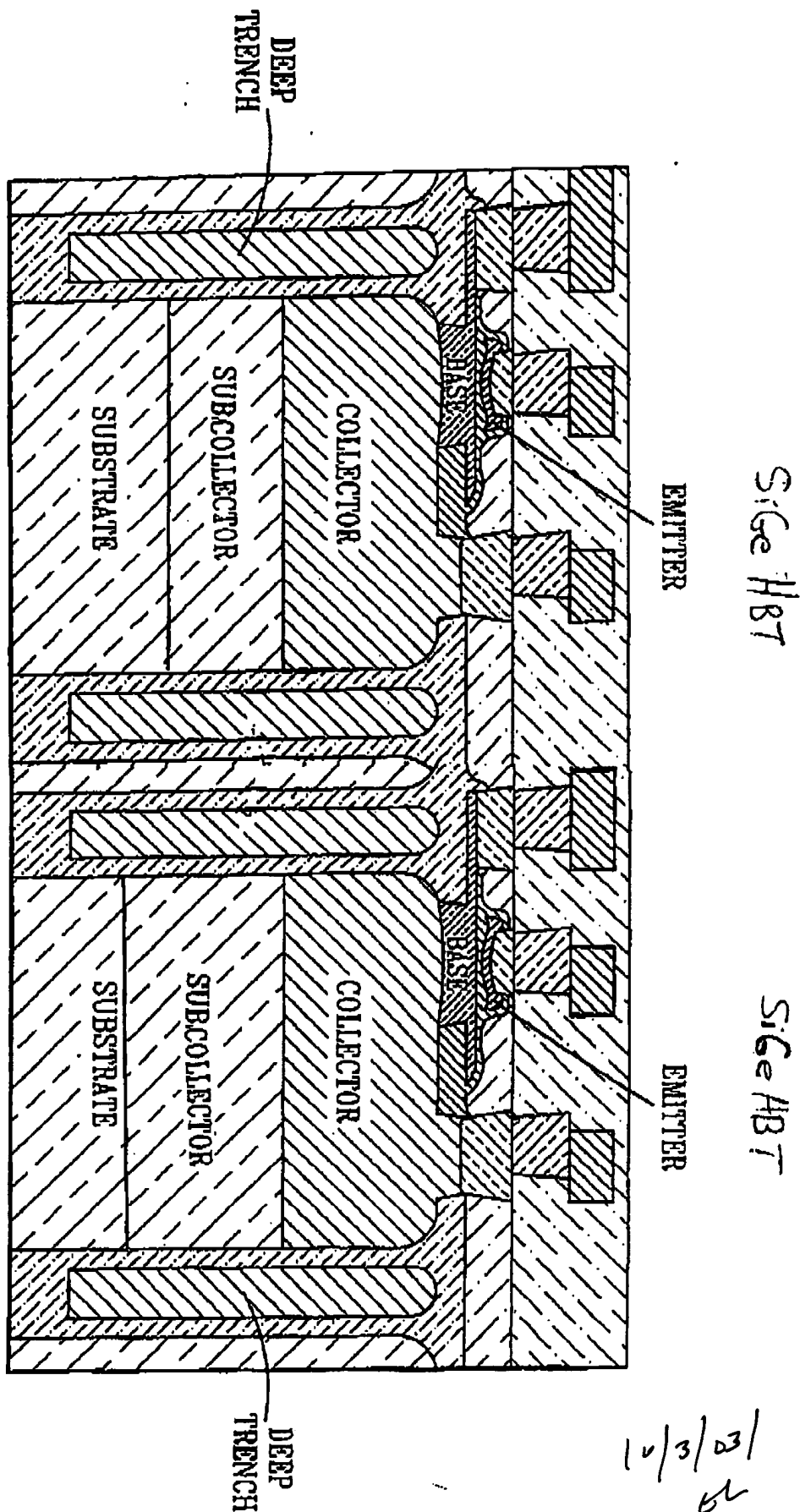


FIG. 21

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EC  
approved

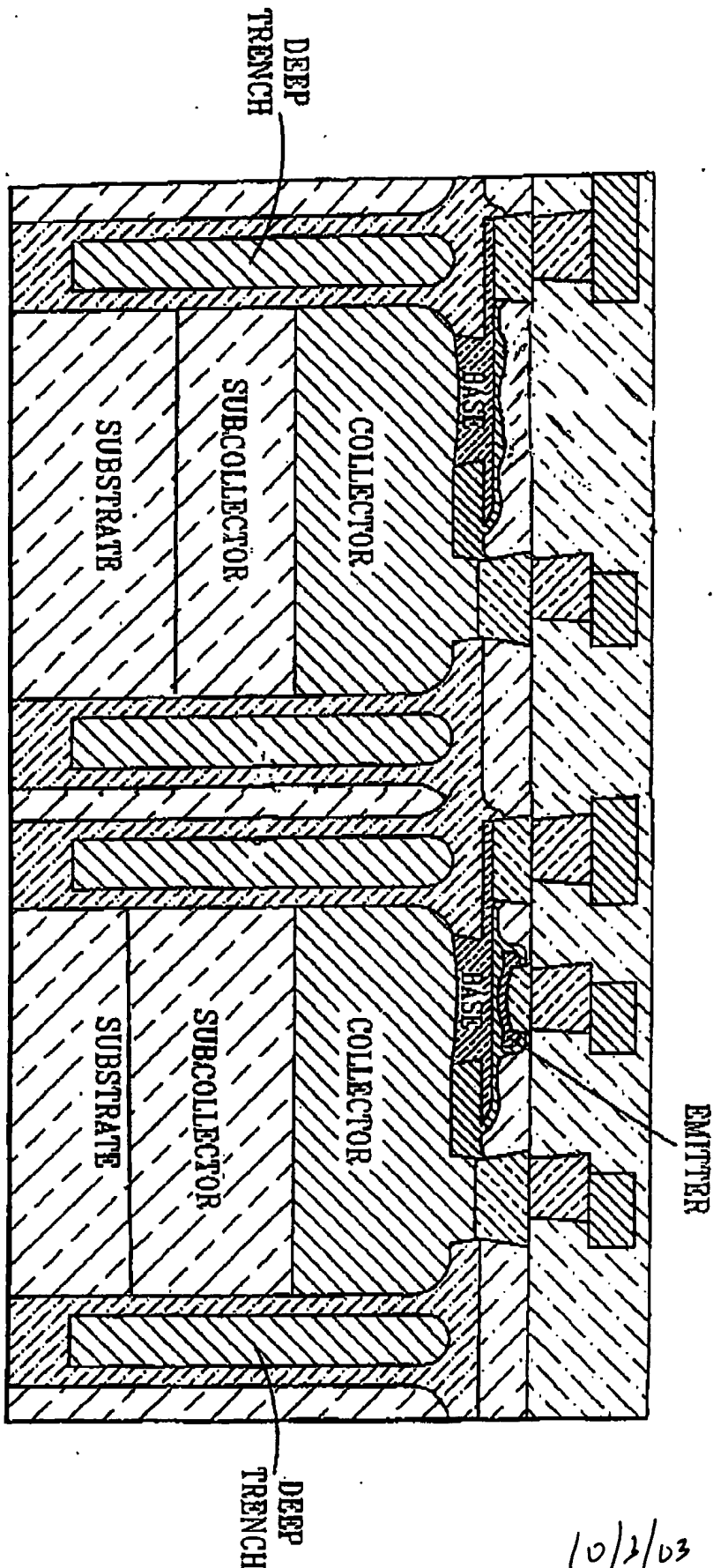




10/3/03/  
62  
approved

Size Vactor

See HBT NPN



7/13/27

10/3/03 el  
approved